


FS5ASJ-2

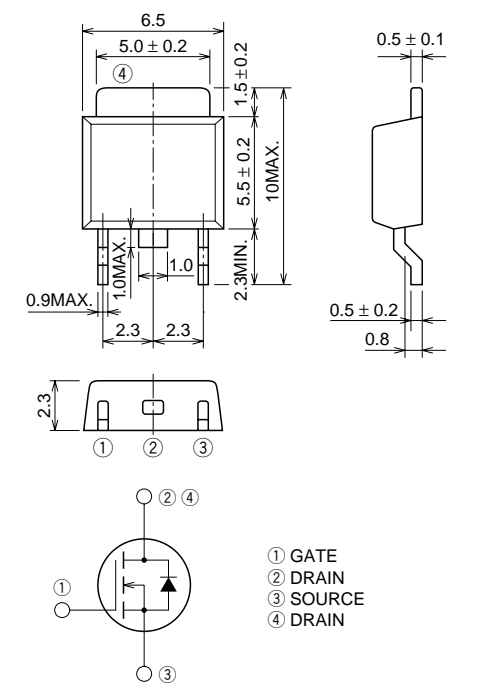
HIGH-SPEED SWITCHING USE

FS5ASJ-2



- 4V DRIVE
- V_{DSS} 100V
- $r_{DS(ON)}$ (MAX) 0.4Ω
- I_D 5A
- Integrated Fast Recovery Diode (TYP.) 80ns

OUTLINE DRAWING Dimensions in mm



MP-3

APPLICATION

Motor control, Lamp control, Solenoid control
DC-DC converter, etc.

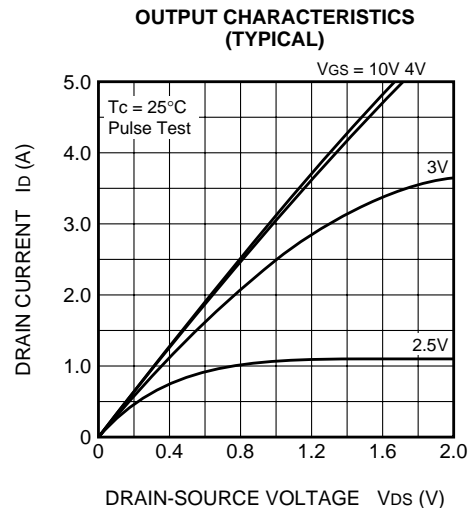
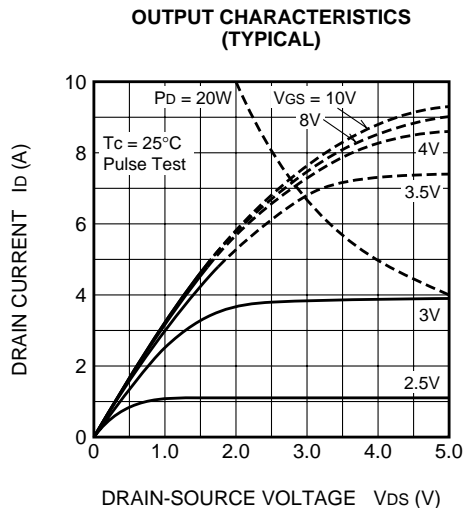
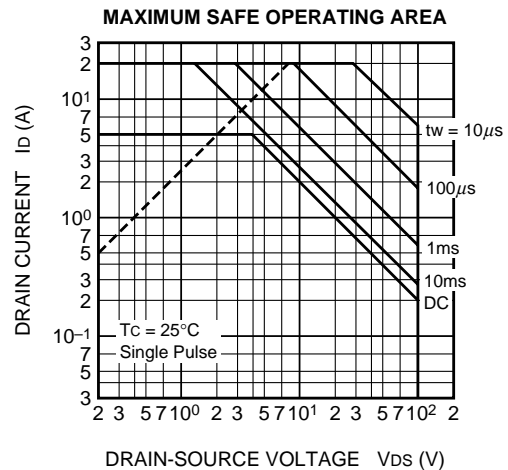
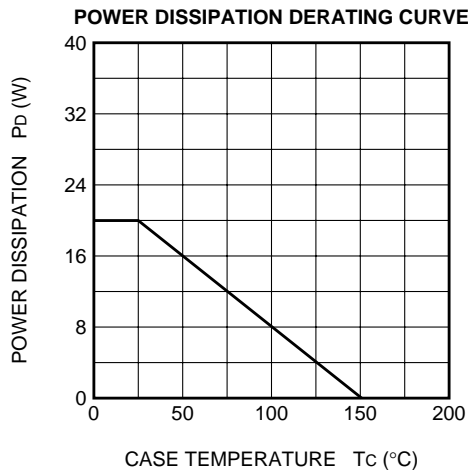
MAXIMUM RATINGS ($T_c = 25^\circ\text{C}$)

Symbol	Parameter	Conditions	Ratings	Unit
V_{DSS}	Drain-source voltage	$V_{GS} = 0V$	100	V
V_{GSS}	Gate-source voltage	$V_{DS} = 0V$	± 20	V
I_D	Drain current		5	A
I_{DM}	Drain current (Pulsed)		20	A
I_{DA}	Avalanche drain current (Pulsed)	$L = 100\mu\text{H}$	5	A
I_S	Source current		5	A
I_{SM}	Source current (Pulsed)		20	A
P_D	Maximum power dissipation		20	W
T_{ch}	Channel temperature		$-55 \sim +150$	$^\circ\text{C}$
T_{stg}	Storage temperature		$-55 \sim +150$	$^\circ\text{C}$
—	Weight	Typical value	0.26	g

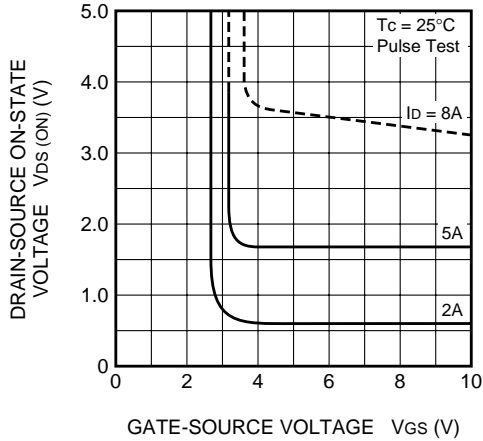
ELECTRICAL CHARACTERISTICS (Tch = 25°C)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
V (BR) DSS	Drain-source breakdown voltage	Id = 1mA, Vgs = 0V	100	—	—	V
IgSS	Gate-source leakage current	Vgs = ±20V, Vds = 0V	—	—	±0.1	μA
IbSS	Drain-source leakage current	Vds = 100V, Vgs = 0V	—	—	0.1	mA
VGS (th)	Gate-source threshold voltage	Id = 1mA, Vds = 10V	1.0	1.5	2.0	V
rDS (ON)	Drain-source on-state resistance	Id = 2A, Vgs = 10V	—	0.31	0.40	Ω
rDS (ON)	Drain-source on-state resistance	Id = 2A, Vgs = 4V	—	0.34	0.46	Ω
VDS (ON)	Drain-source on-state voltage	Id = 2A, Vgs = 10V	—	0.62	0.8	V
yfs	Forward transfer admittance	Id = 2A, Vds = 5V	—	6	—	S
Ciss	Input capacitance	Vds = 10V, Vgs = 0V, f = 1MHz	—	360	—	pF
Coss	Output capacitance		—	75	—	pF
Crss	Reverse transfer capacitance		—	20	—	pF
td (on)	Turn-on delay time	VDD = 50V, Id = 2A, Vgs = 10V, RGEN = RGS = 50Ω	—	10	—	ns
tr	Rise time		—	7	—	ns
td (off)	Turn-off delay time		—	35	—	ns
tf	Fall time		—	15	—	ns
VSD	Source-drain voltage	Is = 2A, Vgs = 0V	—	1.0	1.5	V
Rth (ch-c)	Thermal resistance	Channel to case	—	—	6.25	°C/W
trr	Reverse recovery time	Is = 5A, dis/dt = -100A/μs	—	80	—	ns

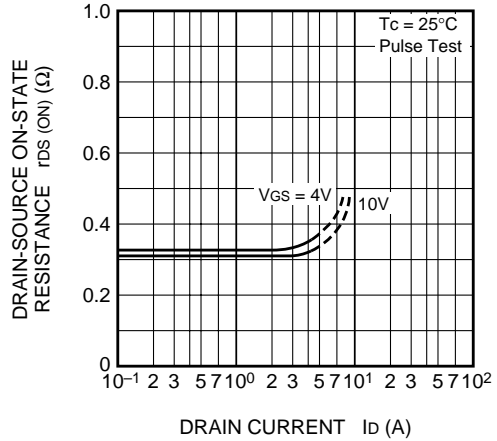
PERFORMANCE CURVES



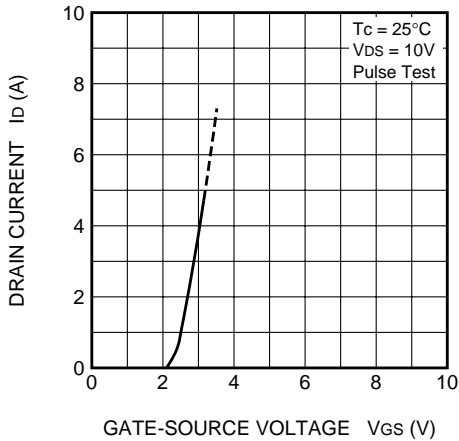
ON-STATE VOLTAGE VS. GATE-SOURCE VOLTAGE (TYPICAL)



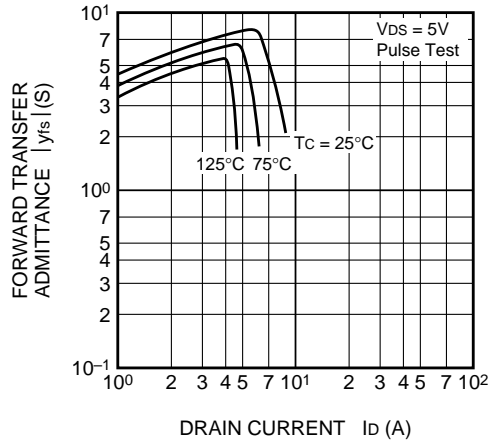
ON-STATE RESISTANCE VS. DRAIN CURRENT (TYPICAL)



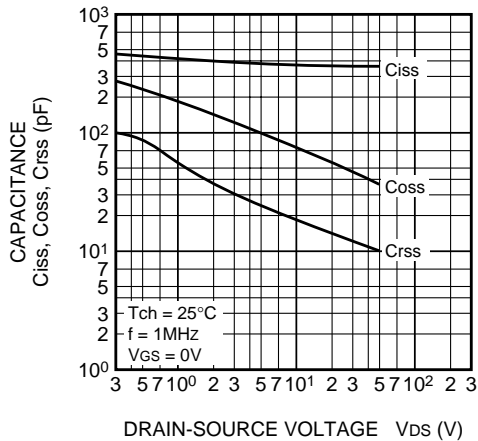
TRANSFER CHARACTERISTICS (TYPICAL)



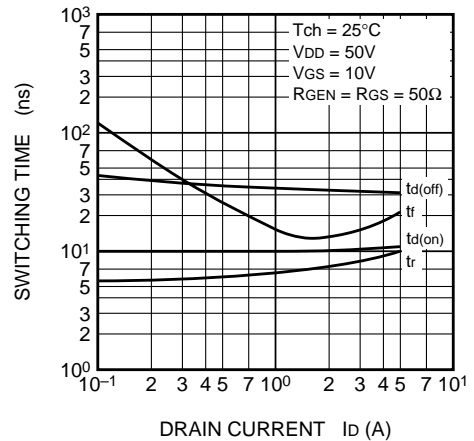
FORWARD TRANSFER ADMITTANCE VS. DRAIN CURRENT (TYPICAL)



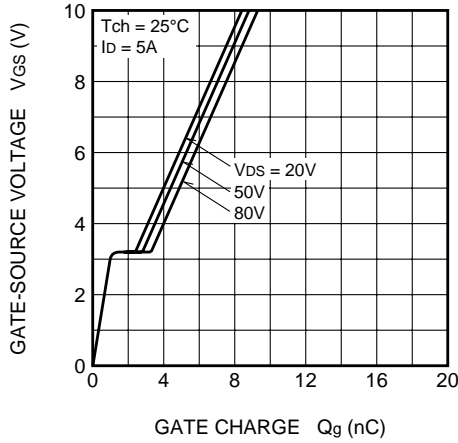
CAPACITANCE VS. DRAIN-SOURCE VOLTAGE (TYPICAL)



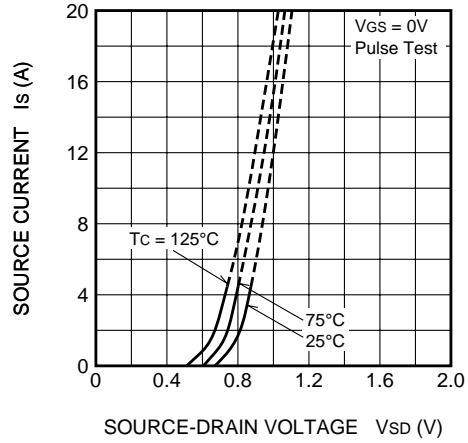
SWITCHING CHARACTERISTICS (TYPICAL)



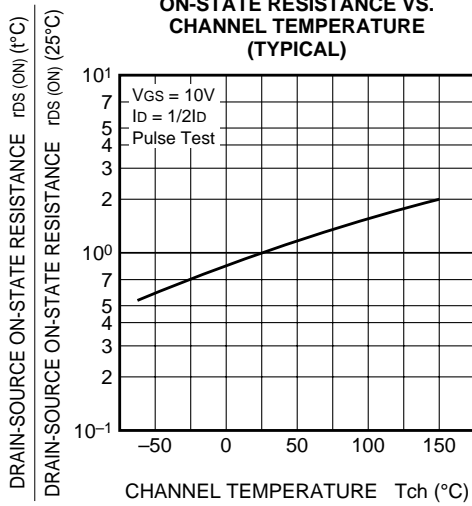
GATE-SOURCE VOLTAGE VS. GATE CHARGE (TYPICAL)



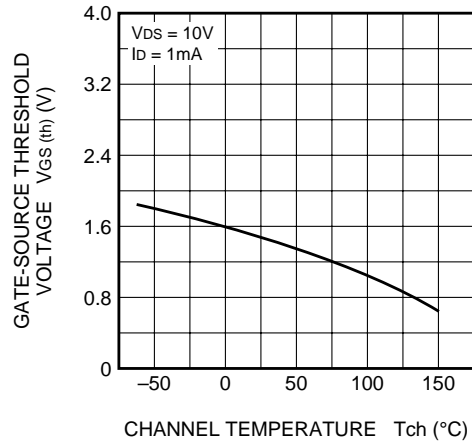
SOURCE-DRAIN DIODE FORWARD CHARACTERISTICS (TYPICAL)



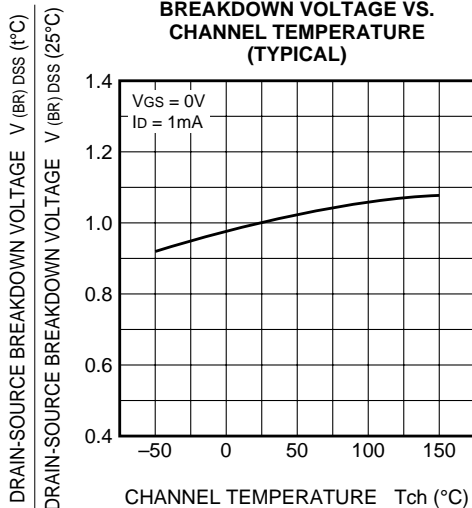
ON-STATE RESISTANCE VS. CHANNEL TEMPERATURE (TYPICAL)



THRESHOLD VOLTAGE VS. CHANNEL TEMPERATURE (TYPICAL)



BREAKDOWN VOLTAGE VS. CHANNEL TEMPERATURE (TYPICAL)



TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS

